

ABSTRACT

A method of manufacturing a group III-V crystal is made available by which good-quality group III-V crystals are easily obtained at low cost without causing cracks, even when using a variety of substrates. A method of manufacturing a group III-V crystal, characterized in including: a step of depositing a metal film (2) on a substrate (1); a step of heat-treating the metal film (2) in an atmosphere in which a patterning compound is present; and a step of growing a group III-V crystal (4) on the metal film after the heat treatment. Additionally, a method of manufacturing a group III-V crystal, characterized in including: a step of growing a group III-V compound buffer film on the metal film after the heat treatment; and a step of growing a group III-V crystal on the group III-V compound buffer film.